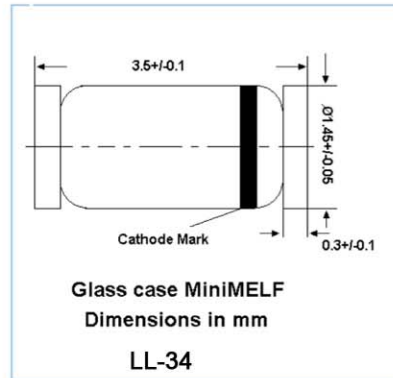


Fast switching diode in MiniMELF case especially suited  
**Silicon Epitaxial Planar Switching Diode**

for automatic surface mounting



**Absolute Maximum Ratings (T<sub>a</sub> = 25 °C)**

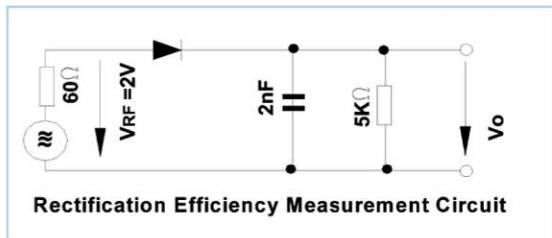
Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V <sub>RM</sub>	100	V
Reverse Voltage	V <sub>R</sub>	75	V
Average Rectified Forward Current	I <sub>F(AV)</sub>	200	mA
Non-repetitive Peak Forward Surge Current	I <sub>FSM</sub>	at t = 1 s	0.5
		at t = 1 ms	1
		at t = 1 μs	4
Power Dissipation	P <sub>tot</sub>	500 <sup>1)</sup>	mW
Junction Temperature	T <sub>j</sub>	175	°C
Storage Temperature Range	T <sub>stg</sub>	- 65 to + 175	°C

<sup>1)</sup> Valid provided that electrodes are kept at ambient temperature.

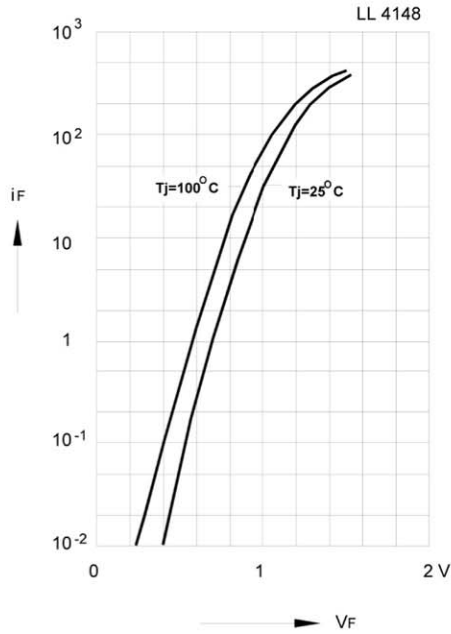
### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 10\text{ mA}$	$V_F$	-	1	V
Leakage Current at $V_R = 20\text{ V}$ at $V_R = 75\text{ V}$ at $V_R = 20\text{ V}, T_J = 150\text{ }^\circ\text{C}$	$I_R$ $I_R$ $I_R$	- - -	25 5 50	nA $\mu\text{A}$ $\mu\text{A}$
Reverse Breakdown Voltage tested with $100\text{ }\mu\text{A}$ Pulses	$V_{(BR)R}$	100	-	V
Capacitance at $V_R = 0, f = 1\text{ MHz}$	$C_{tot}$	-	4	pF
Voltage Rise when Switching ON tested with $50\text{ mA}$ Forward Pulses $t_p = 0.1\text{ s}$ , Rise Time $< 30\text{ ns}$ , $f_p = 5\text{ to }100\text{ KHz}$	$V_{fr}$	-	2.5	V
Reverse Recovery Time at $I_F = 10\text{ mA}$ to $I_R = 1\text{ mA}$ , $V_R = 6\text{ V}$ , $R_L = 100\text{ }\Omega$	$t_{rr}$	-	4	ns
Thermal Resistance Junction to Ambient Air	$R_{thA}$	-	$0.35^{1)}$	K/mW
Rectification Efficiency at $f = 100\text{ MHz}$ , $V_{RF} = 2\text{ V}$	$\eta_V$	0.45	-	-

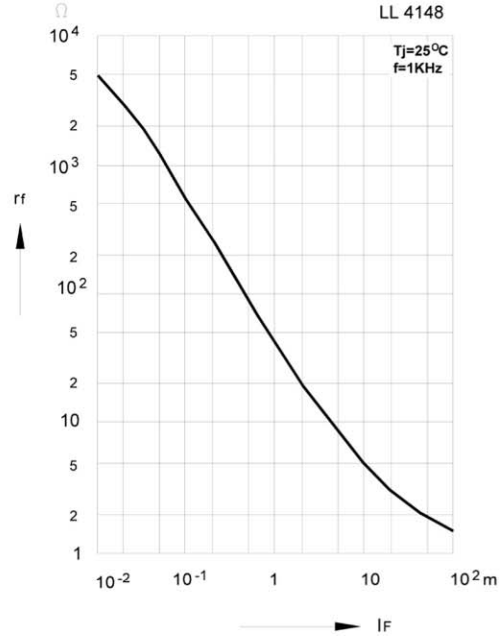
<sup>1)</sup> Valid provided that electrodes are kept at ambient temperature.



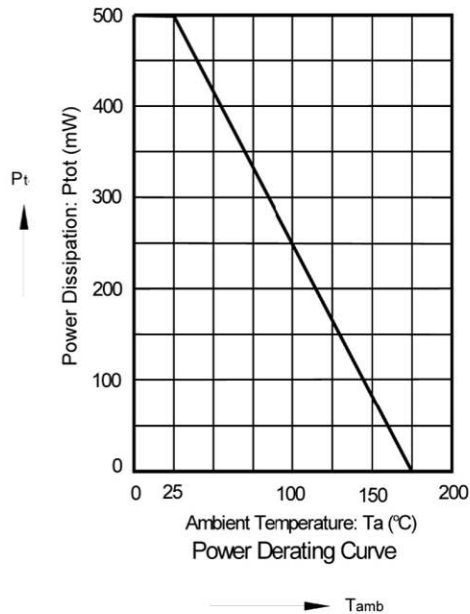
Forward characteristics



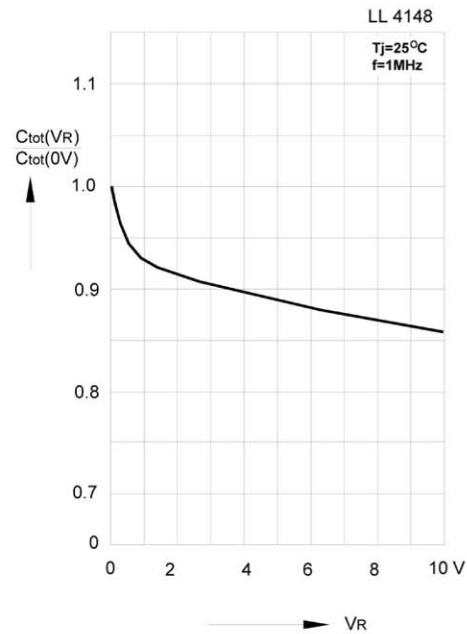
Dynamic forward resistance versus forward current



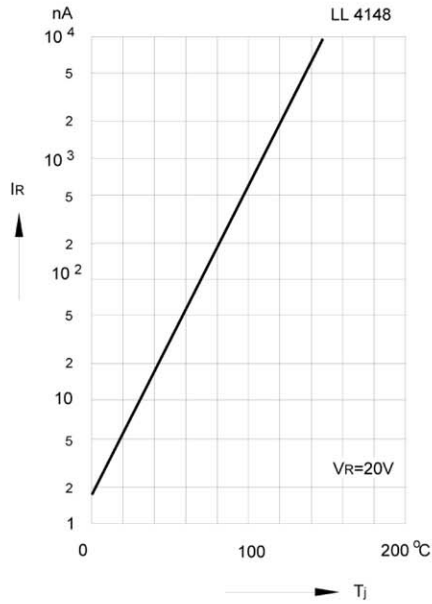
Admissible power dissipation versus ambient temperature  
Valid provided that electrodes are kept at ambient temperature



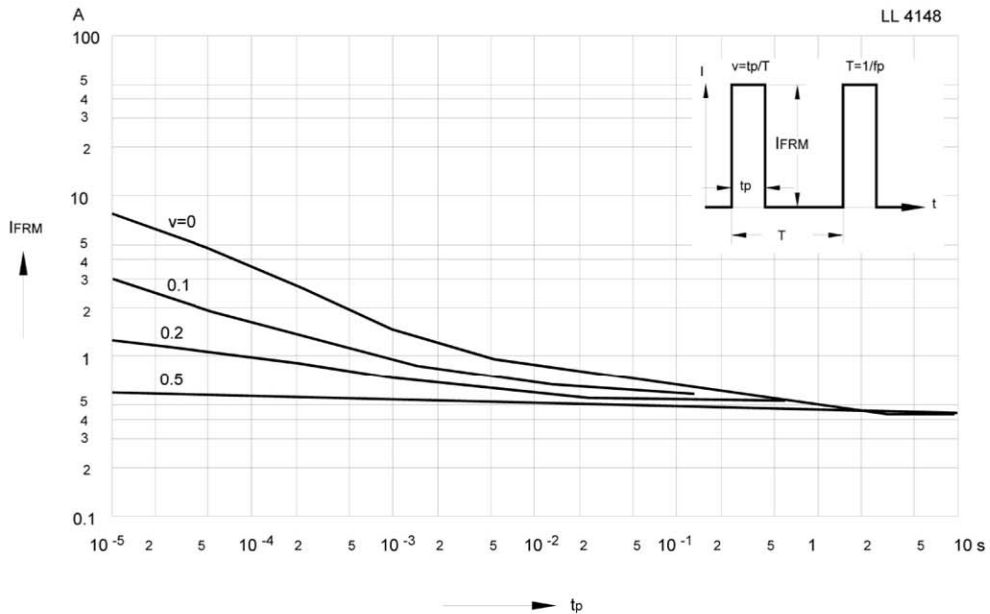
Relative capacitance versus reverse voltage



Leakage current versus junction temperature



Admissible repetitive peak forward current versus pulse duration  
Valid provided that electrodes are kept at ambient temperature



单击下面可查看定价，库存，交付和生命周期等信息

[>>SHIKUES\(时科\)](#)